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(54) **Iridium conductive electrode/barrier structure and method for same**

(57) A conductive barrier, useful as a ferroelectric capacitor electrode, having high temperature stability has been provided. This conductive barrier permits the use of Iridium (Ir) metal in IC processes involving annealing. Separating silicon substrate from Ir film with an intervening, adjacent, tantalum (Ta) film has been found to very effective in suppressing diffusion between layers. The Ir prevents the interdiffusion of oxygen into the silicon during annealing. A Ta or TaN layer prevents the

diffusion of Ir into the silicon. This Ir/TaN structure protects the silicon interface so that adhesion, conductance, hillock, and peeling problems are minimized. The use of Ti overlying the Ir/TaN structure also helps prevent hillock formation during annealing. A method of forming a multilayer Ir conductive structure and Ir ferroelectric electrode are also provided.

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The present search report has been drawn up for all claims			
Place of search THE HAGUE		Date of completion of the search 24 January 2002	Examiner Bailet, B
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<p>CATEGORY OF CITED DOCUMENTS</p> <p>X: particularly relevant if taken alone Y: particularly relevant if combined with another document of the same category A: technological background O: non-written disclosure P: intermediate document</p> <p>T: theory or principle underlying the invention E: earlier patent document, but published on, or after the filing date D: document cited in the application L: document cited for other reasons & : member of the same patent family, corresponding document</p>			

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